风光欣技术资料

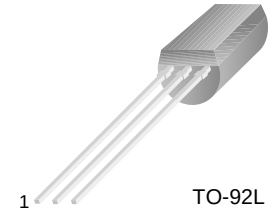
A1273

—PNP silicon —

APPLICATION: High Current Applications.

MAXIMUM RATINGS（Ta＝25℃）

PARAMETER	SYMBOL	RATING	UNIT
Collector-base voltage	VCBO	-30	V
Collector-emitter voltage	VCEO	-30	V
Emitter-base voltage	VEBO	-5	V
Collector current	IC	-2	A
Collector Power Dissipation	PC	1	W
Junction Temperature	TJ	150	℃
Storage Temperature Range	Tstg	－55~150	℃



TO-92L

1. Emitter 2. Collector 3. Base

ELECTRICAL CHARACTERISTICS（Ta=25℃）

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	TEST CONDITION
DC Current Gain	hFE	100		320		VCE= -2 V，Ic= -500 mA
Collector Cut-off Current	ICBO			-0.1	μA	VCB= -30V，IE=0
Emitter Cut-off Current	IEBO			-0.1	μA	VEB= -5 V，Ic=0
Collector-Base Breakdown Voltage	BVCBO	-30			V	Ic= -0.1 mA，IE=0
Collector-Emitter Breakdown Voltage	BVCEO	-30			V	Ic= -10 mA，IB=0
Emitter-Base Breakdown Voltage	BVEBO	-5			V	IE= -0.1 mA，Ic=0
Base-Emitter Voltage	VBE			-1.0	V	VCE= -2 V，Ic= -500 mA
Collector-Emitter Saturation Voltage	VCE(sat)			-2.0	V	Ic= -1.5 A，IB= -30 mA
Gain bandwidth product	fT		120		MHz	Ic= -500 mA，VCE= -2 V
Common Base Output Capacitance	Cob		48		PF	VCB= -10 V，IE=0，f = 1 MHz

hFE **Classification**

Classification	O	Y
hFE	100～ 200	160 ～320